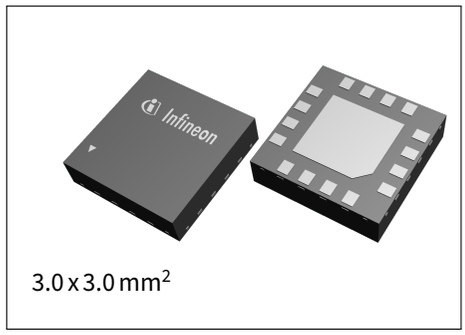
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BGAP2S30A

Pre-Driver for Wireless Infrastructure Applications

1 Features

- Operation frequency range: 3300 to 4200MHz
- Gain: 35dB
- Output P1dB: 28.5dBm
- 50Ω single-ended input and output
- 5V supply voltage
- TSNP-16 leadless package (3.0 x 3.0 mm^2)
- BiCMOS Technology



3.0 x 3.0 mm^2

2 Potential Applications

- 4G/5G
- Cellular Infrastructure
  - Massive MIMO systems
  - Small cells

3 Product Validation

RoHS Halogen-Free Lead-Free Green

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

4 Description

The product is a stand-alone pre-driver in package. The pre-driver is a two-stage amplifier designed to be used in the 5G Tx line-up for base station applications as the pre-driver for the Doherty power amplifier. It has been designed in the INFINEON BiCMOS technology. Input and outputs are 50Ω single-ended.
The device configuration is shown in Fig. 1.

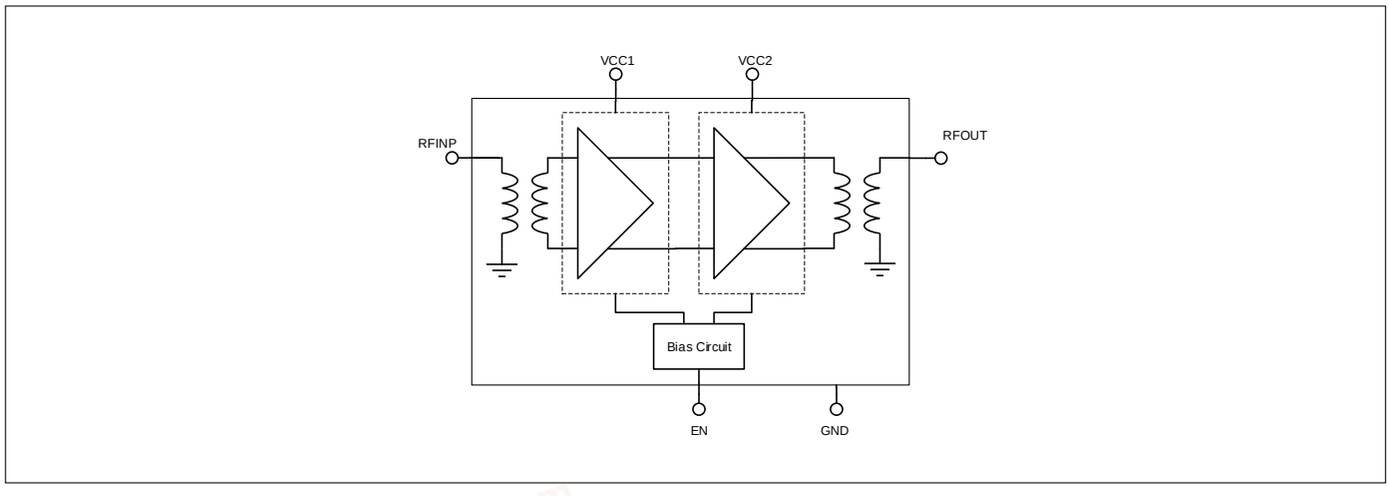


Figure 1: BGAP2S30A Block diagram

Product Name	Marking	Package
BGAP2S30A	BP2S3A YYWW(YY=year, WW=week)	PG-TSNP-16-12

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5 Absolute Maximum Ratings

Table 1: Absolute Maximum Ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply Voltage	V_{CC}	-0.5	–	5.5	V	[1]
Enable Voltage	V_{EN}	-0.4	–	4.0	V	–
Storage Temperature	T_{STG}	-45	–	150	°C	–
Junction Temperature	T_J	-40	–	170	°C	–
DC voltage on RF Ports	$V_{RF,DC}$	0	–	0	V	[1]
RF Input Power CW	$P_{IN,CW}$	–	–	6	dBm	–
ESD Capability HBM [2]	$V_{ESD,HBM}$	-1000	–	1000	V	–
ESD Capability CDM [3]	$V_{ESD,CDM}$	-250	–	250	V	–

[1] All voltages refer to GND-Nodes unless otherwise noted
[2] Human Body Model ANSI/ESDA/JEDECJS-001 (R = 1.5kΩ, C = 100pF)
[3] Field-Induced Charged-Device Model ANSI/ESDA/JEDECJS-002. Simulates charging/discharging events that occur in production equipment and processes. Potential for CDM ESD events occurs whenever there is metal-to-metal contact in manufacturing.

Warning: Stresses above the max. values listed here may cause permanent damage to the device. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit. Exposure to conditions at or below absolute maximum rating but above the specified maximum operation conditions may affect device reliability and life time. Functionality of the device might not be given under these conditions.

Table 2: Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance - Junction - Solder pad (@25°C)	$R_{th,JS}$	19.6	°K/W

Table 3: Recommended Operating Conditions

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply Voltage	V_{CC}	4.75	–	5.25	V	–
Enable Voltage OFF	$V_{EN,OFF}$	0	–	0.63	V	–
Enable Voltage ON	$V_{EN,ON}$	1.17	–	3.6	V	–
Operating Temperature	T_A	-40	–	115	°C	Solder joint temperature

Power-up and power-down sequences
The following sequences are required to be respected during power-up/down of the device.
Power-up sequence: 1. VCC1 and VCC2 -> on; 2. EN -> on.
Power-down sequence: 1. EN -> off; 2. VCC1 and VCC2 -> off.
Deviating from these sequences may cause permanent damage.

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6 Electrical Characteristics

Table 4: Electrical Characteristics. Test conditions (unless otherwise noted): T=25°C, V_{CC}=5V, f_{RF}=3.6GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
RF Frequency	f_{RF}	3300	–	4200	MHz	–
Current Consumption OFF	$I_{CC,OFF}$	–	1.2	–	mA	–
Current Consumption ON	$I_{CC,ON}$	–	121	–	mA	No RF input signal
Input Return Loss	RL_{IN}	8	18	–	dB	–
Output Return Loss	RL_{OUT}	15	17	–	dB	–
Gain	G	34.1	35	–	dB	–
Gain Flatness	G_{FLAT}	–	–	0.4	dB	Defined in any 100MHz within band
Output P1dB	OP_{1dB}	28	28.5	–	dBm	–
Output IP3	OIP_3	33.7	34.1	–	dBm	P_{IN1}=P_{IN2}=-25dBm, Δf=1MHz
Adjacent Channel Leakage Ratio	$ACLR$	–	-48.6	-45	dBc	20MHz E-TM1.1 with 9.8 dB PAPR @Pout=15 dBm
Noise Figure	NF	–	3.2	3.7	dB	–
Switching ON Time	T_{ON}	–	0.45	0.5	μs	P_{OUT} to 90% of final value
Switching OFF Time	T_{OFF}	–	–	0.3	μs	Gain within <5% and power dissipation <10% than in ON state

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7 Application Information

Pin Configuration and Function

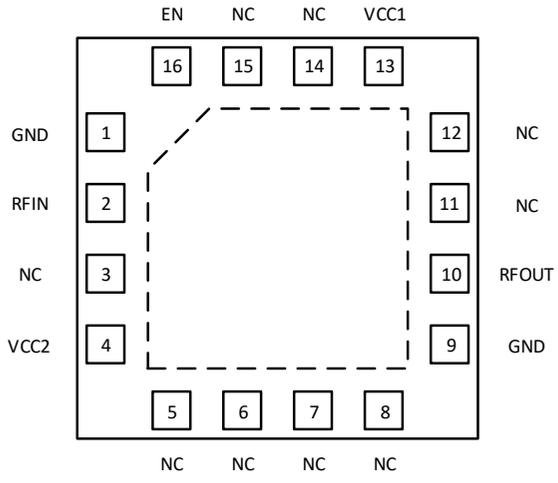


Figure 2: BGAP2S30A Pin Configuration - Top View

Table 5: Pin Definition and Function

Pin No.	Name	Function
1, 9	GND	Ground
2	RFIN	RF Input
4	VCC2	2nd stage DC voltage supply
3, 5, 6, 7, 8, 11, 12, 14, 15	NC	Not connected internally. It can be either left floating or connected to ground
10	RFOUT	RF Output
13	VCC1	1st stage DC voltage supply
16	EN	Chip enable
Backside Paddle	GND	Ground connection

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Application Board Configuration

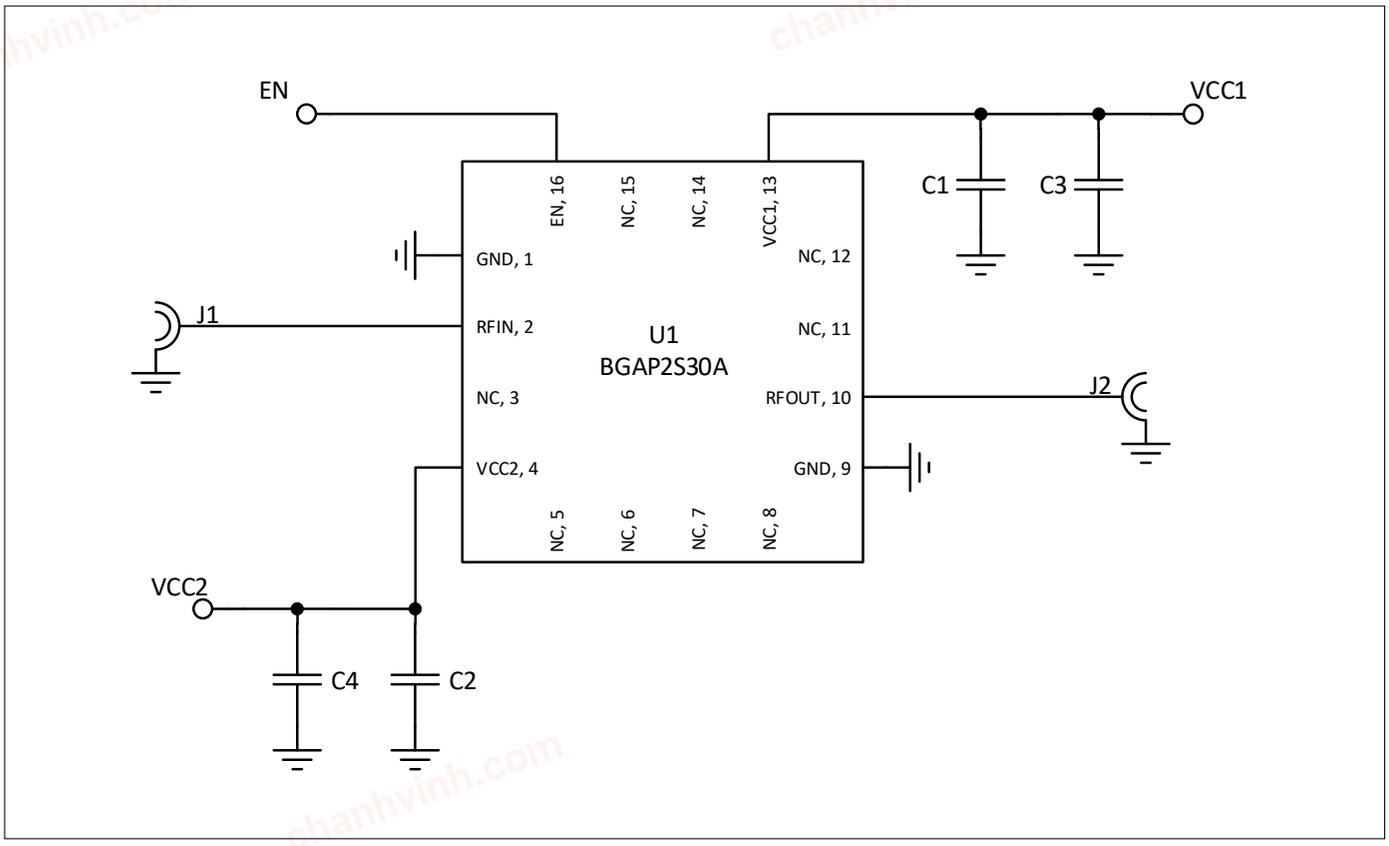


Figure 3: BGAP2S30A Application Schematic

Table 6: Bill of Materials Table

Name	Value	Description	Part Number	Manufacturer
C1, C2	10nF	Capacitor, X7R, 0402	–	Various
C3, C4	1uF	Capacitor, X7R, 0402	–	Various
J1, J2	–	Connector, SMA	–	Various
U1	–	Pre-driver, PG-TSNP-16-12	BGAP2S30A	Infineon

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8 Package Information

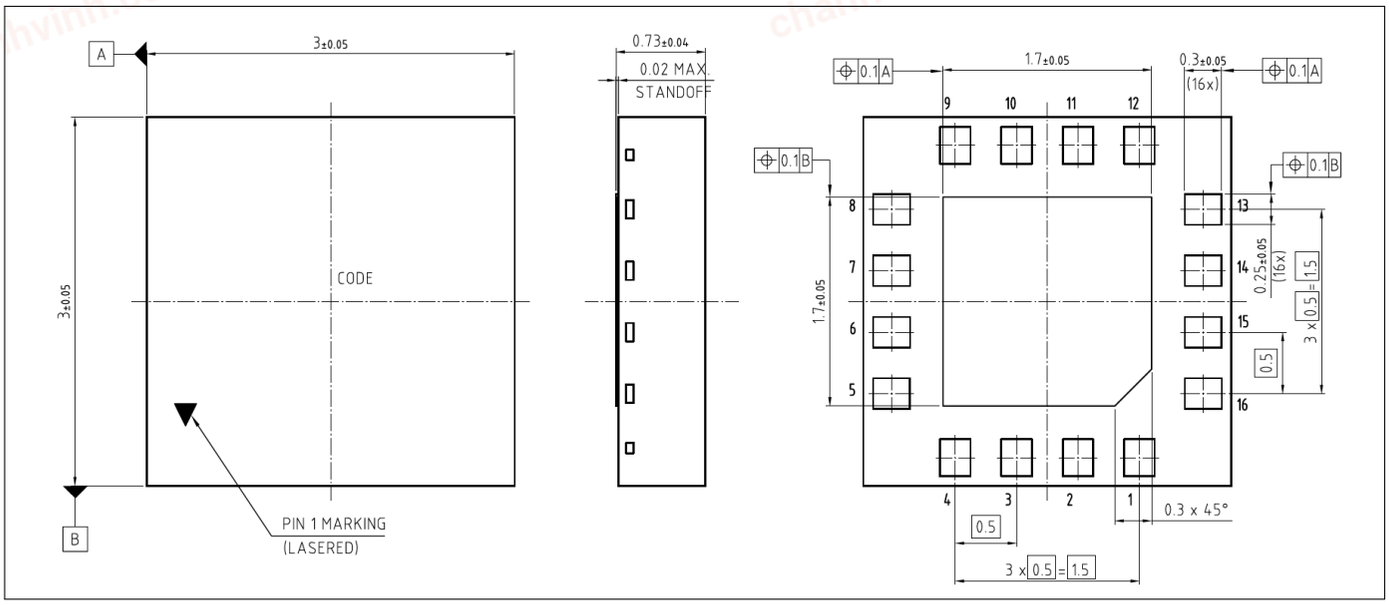


Figure 4: PG-TSNP-16-12 Package Outline (3.0mm x 3.0mm x 0.73mm)

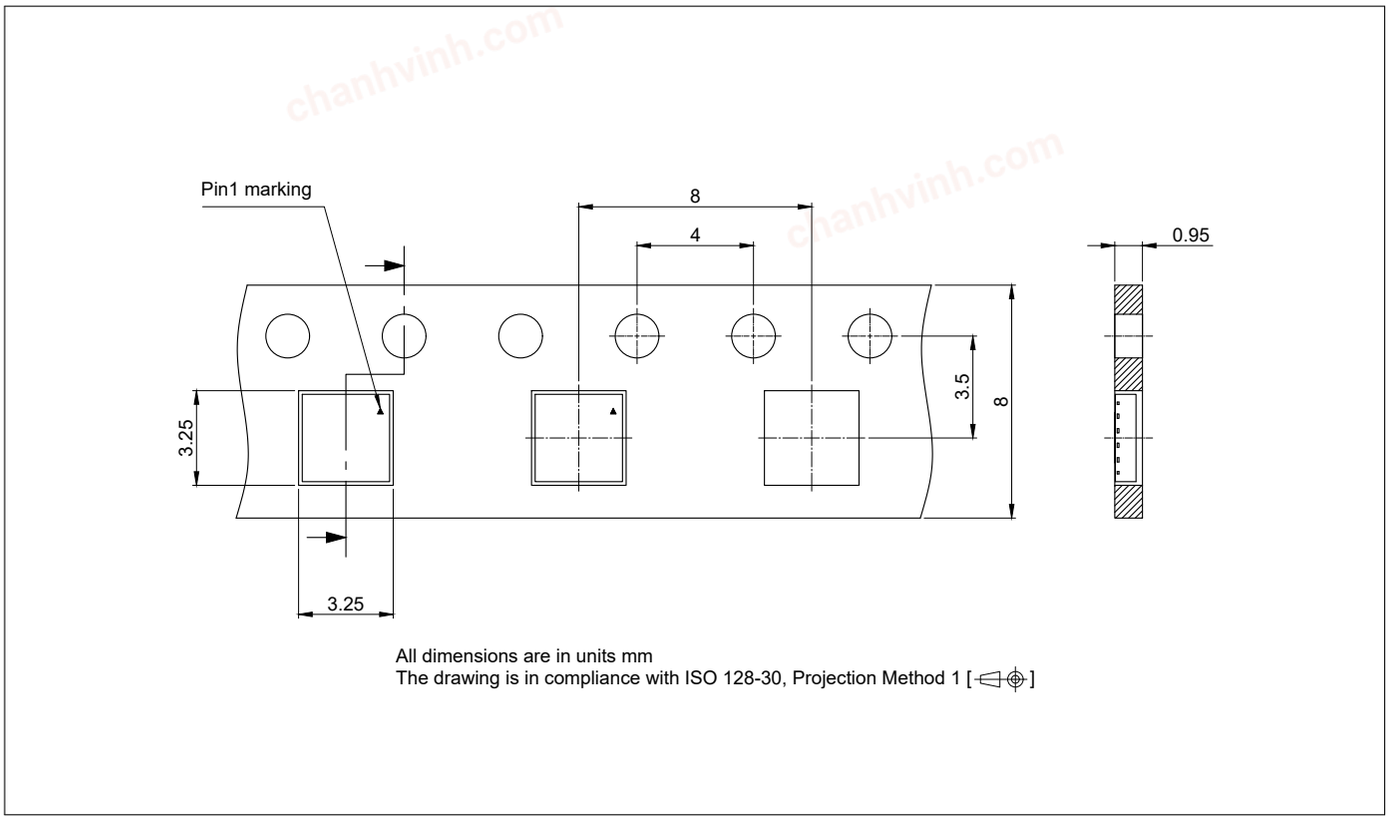


Figure 5: PG-TSNP-16-12 Carrier Tape

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Revision History	
Page or Item	**Subjects (major changes since previous revision)**
all	Preliminary, Revision v1.0 - 2023-06-01
all	Preliminary, Revision v1.1 - 2023-08-03 Package changed to 16-12

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